

WHAT IS CLAIMED IS:

*Sub 1* 1. A method of manufacturing a semiconductor device, comprising the steps of:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film; and

irradiating the first crystalline semiconductor film with a second laser beam to form a second crystalline semiconductor film.

2. A method according to claim 1, wherein the first laser beam and the second laser beam are different in wavelength from each other.

*Sub 2* 3. A method of manufacturing a semiconductor device, comprising the steps of:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film; and

irradiating the first crystalline semiconductor film with a second laser beam to form a second crystalline semiconductor film, wherein

the first laser beam is 126 to 370 nm in wavelength.

4. A method of manufacturing a semiconductor device, comprising the steps of:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film;

and

irradiating the first crystalline semiconductor film with a second laser beam to form a second crystalline semiconductor film, wherein

the second laser beam is 370 to 650 nm in wavelength.

5. A method of manufacturing a semiconductor device, comprising the steps of:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film;

and

irradiating the first crystalline semiconductor film with a second laser beam to form a second crystalline semiconductor film, wherein

the first laser beam is 126 to 370 nm in wavelength whereas the second laser beam is 370 to 650 nm in wavelength.

Subsidiary

6. A method according to claim 1, wherein the semiconductor device is a liquid crystal display device or a light emitting device.

7. A method according to claim 1, wherein the semiconductor device is a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

8. A method according to claim 3, wherein the semiconductor device is a liquid crystal display device or a light emitting device.

9. A method according to claim 3, wherein the semiconductor device is a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

10. A method according to claim 4, wherein the semiconductor device is a liquid crystal display device or a light emitting device.

11. A method according to claim 4, wherein the semiconductor device is a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD

player, an electronic book, or a portable information terminal.

12. A method according to claim 5, wherein the semiconductor device is a liquid crystal display device or a light emitting device.

13. A method according to claim 5, wherein the semiconductor device is a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.